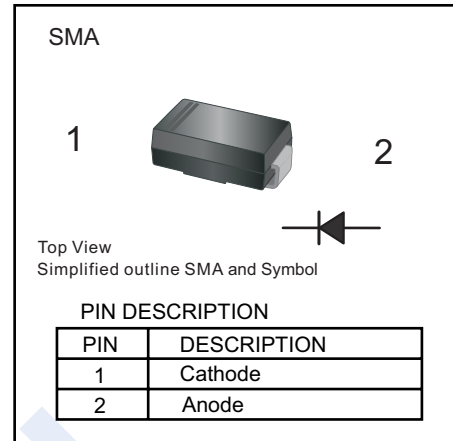


Fast Recovery Diodes

ES1A ~ ES1J

■ Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	ES1A	ES1B	ES1C	ES1D	ES1E	ES1G	ES1J	Unit
Repetitive Peak Reverse Voltage	VRRM								V
Working Peak Reverse Voltage	VRWM	50	100	150	200	300	400	600	
Maximum DC Blocking Voltage	VDC								
RMS Reverse Voltage	VR(RMS)	35	70	105	140	210	280	420	
Forward Voltage @ IF=1A	VF	0.95			1.25		1.7		
Average Rectified Output Current TL=120°C	Io	1							A
Peak Forward Surge Current @ 8.3ms	IFSM	30							
Maximum DC Reverse Current Ta=25°C Ta=100°C	IR	5							μA
		500							
Reverse Recovery Time (Note.1)	trr	35							ns
Typical Junction Capacitance (Note.2)	Cj	10							pF
Thermal Resistance.Junction- to-Lead	RthJL	35							°C/W
Junction Temperature	Tj	150							°C
Storage Temperature	Tstg	-65 to 150							

Note.1: Measured with IF= 0.5A, IR = 1A, Irr = 0.25A. See figure 5.

Note.2: Measured at 1 MHz and Applied VR=4V

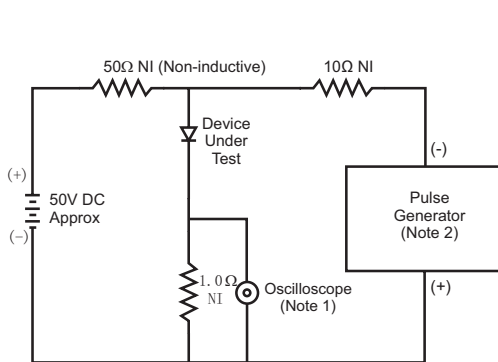
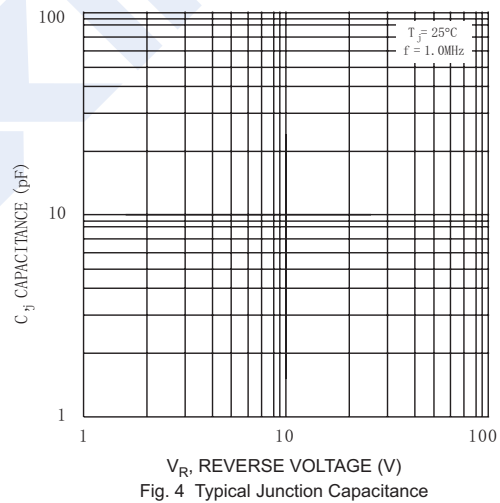
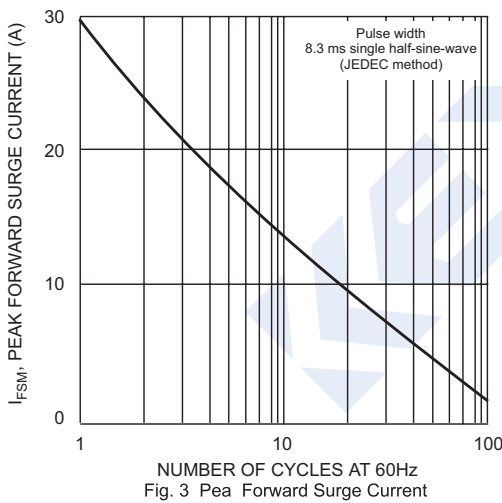
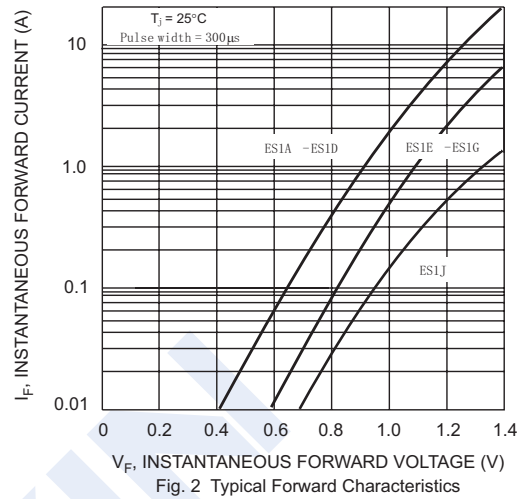
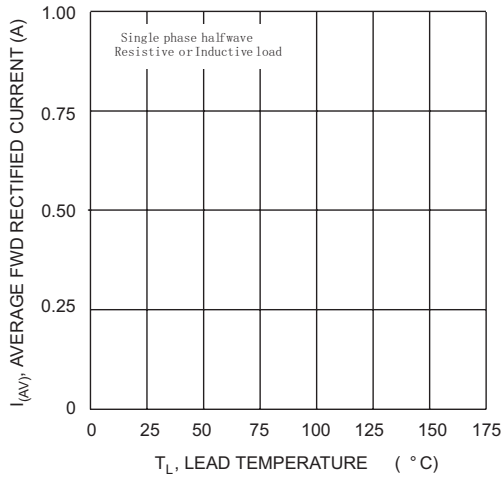
■ Marking

NO.	ES1A	ES1B	ES1C	ES1D	ES1E	ES1G	ES1J
Marking	ES1A	ES1B	ES1C	ES1D	ES1E	ES1G	ES1J

Fast Recovery Diodes

ES1A ~ ES1J

■ Typical Characteristics



- Notes:
 1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
 2. Rise Time = 10ns max. Input Impedance = 50Ω.

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

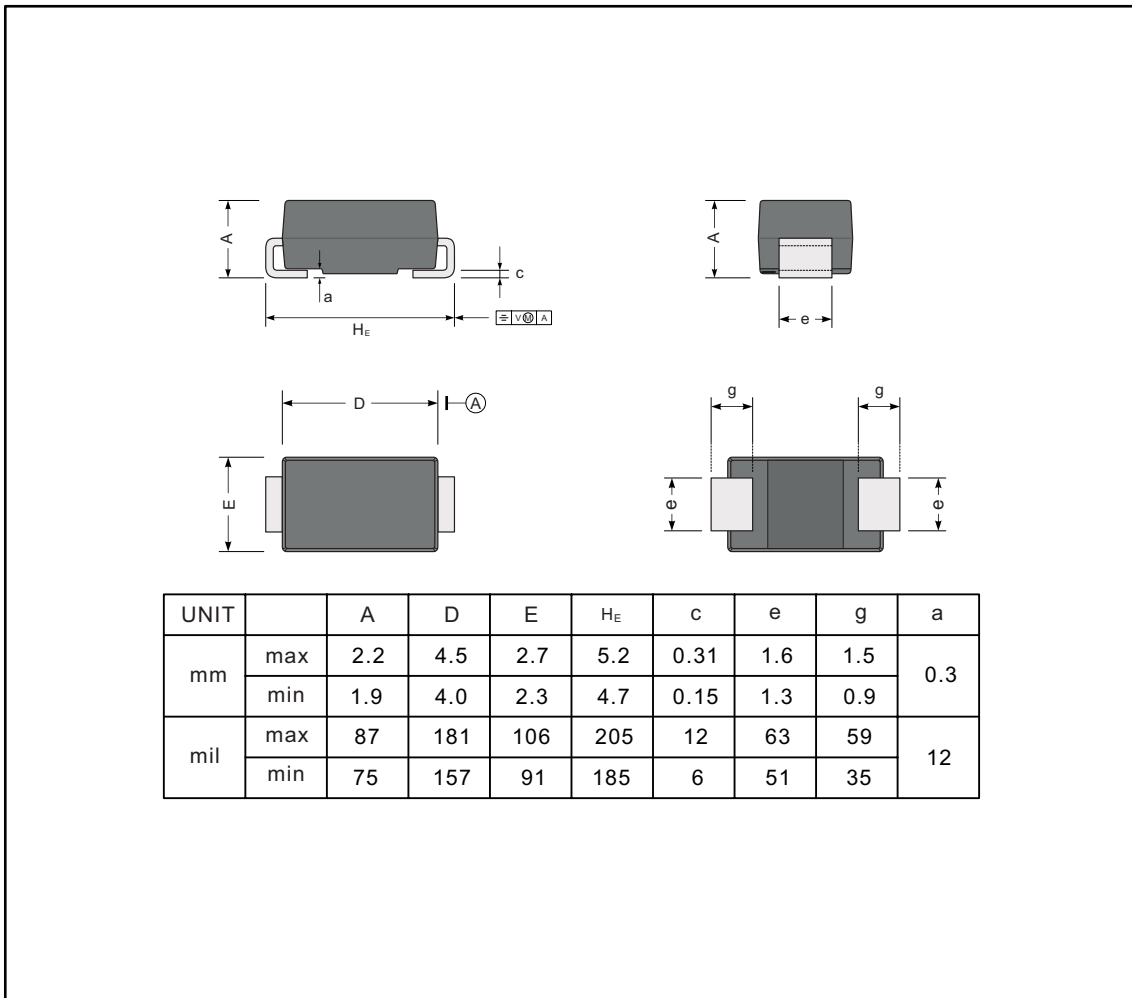
Fast Recovery Diodes

ES1A ~ ES1J

■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SMA



■ The recommended mounting pad size

